



Silicon Crystal & Compound Semiconductor

↘ CZ Single Crystal Silicon Wafer

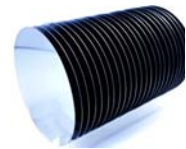
CZ Single Crystal Silicon Wafer, sliced from CZ monocrystalline silicon ingot, with low defects density or thickness variation, but flexible resistivity range and thickness for different sizes. Mostly being used for fabrication of diodes, transistors, discrete components in electronic industry, but also suitable for advanced wafer processes, including diffusion, epitaxy or semi-insulating. Dopant as Boron, Phosphorus, Arsenic or Antimony can be introduced to transform into P-type or N-type conductivity wafer. 2" 3" 4" 5" 6" 8" and 12" As-cut, lapped, etched or polished wafer is available.



No.	Items	Standard Specifications				
1	Size	2"	4"	6"	8"	12"
2	Diameter	50.8	100	150	200	300
3	Conductivity	P/N	P/N	P/N	P/N	P/N
4	Orientation	<100>, <110>, <111>				
5	Thickness	μm	279, 381, 425, 525, 575, 625, 675, 725, 775 or as required			
6	Resistivity	Ω.cm	≤0.005, 0.005-1, 1-10, 10-20, 20-100, 100-300 etc			
7	RRV	max	8%, 10%, 12%, or as required			
8	Primary Flat/Length	mm	<110>±1° or required, as per SEMI standard			
9	Secondary Flat/Length	mm	As per SEMI standard or required			
10	TTV	μm max	10	10	10	10
11	Bow/Warp	μm max	30	30	30	30
12	Surface Finish		As-cut, L/L, P/E, P/P etc			
13	Packing		Foam box or cassette inside, carton box outside			

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MCZ Single Crystal Silicon Wafer, magnetic field-applied method added, enabling a lower oxygen content and dislocation, also can be used in electronic or photovoltaic industries. 2" 3" 4" 5" 6" and 8" can be supplied.



No.	Items	Standard Specifications				
1	Size	2"	3"	4"	6"	8"
2	Diameter	50.8	76.2	100	150	200
3	Conductivity	P/N	P/N	P/N	P/N	P/N
4	Orientation	<100>, <110>, <111>				
5	Thickness	μm	180, 279, 381, 425, 525, 575, 675, 725 or as required			
6	Resistivity	Ω.cm	≤0.005, 0.005-1, 1-10, 10-20, 20-100, 100-300 etc			
7	RRV	max	8%, 10%, 12%, or as required			
8	TTV	μm max	10	10	10	10
9	Bow/Warp	μm max	30	30	30	30
10	Carbon Content	a/cm ³ max	5E16	5E16	5E16	5E16
11	Oxygen Content	a/cm ³ max	1E18	1E18	1E18	1E18
12	Dislocation	cm ⁻² max	100	100	100	100
13	Surface Finish		As-cut, L/L, P/E, P/P etc			
14	Packing		Foam box or cassette inside, carton box outside			

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